

# 2012 Collaborative Conference on Crystal Growth (3CG)

December 11-14, 2012

Doubletree by Hilton Orlando at SeaWorld, Orlando, Florida,  
USA

## Conference Onsite Registration

Conference Hotel

14:30 PM - 18:00 PM

December 10

<b>Tuesday December 11 8:20 - 8:30 AM</b>	<b>Opening: NANO</b>	
<b>Tuesday December 11</b>	<b>Room A: Session I</b>	<b>Chair: Nong-Moon Hwang</b>
8:30 - 8:55 AM	A01: Epitaxial Growth of AlN and Related Alloys	Mitsuru Funato Kyoto University, Japan
8:55 - 9:20 AM	A02: Growth of Quantum Wire III-N Nanostructures	Bruno Daudin CEA-Grenoble, INAC SP2M/NPSC, France
9:20 - 9:45 AM	A03: GaN Nanowires Seeded by Al Droplets on Si (111) : Control of Polarity and Chronology of Their Elongation	Ludovic Largeau LPN-CNRS, France
9:45 - 10:10 AM	A04: MOVPE Growth of InN-based Alloys, InGaN and InAlN, With Intermediate In Compositions	Akio Yamamoto University of Fukui, Japan
10:10 - 10:30 AM	<b>COFFEE BREAK</b>	
<b>Tuesday December 11</b>	<b>Room A: Session II</b>	<b>Chair: Bruno Daudin</b>
10:30 - 10:55 AM	A05: In Situ Synchrotron Studies of Oxide Thin Film Synthesis	Dillon D. Fong Argonne National Laboratory, USA

10:55 - 11:20 AM	A06: Self-induced Formation Mechanisms of GaN Nanowires Grown by Molecular Beam Epitaxy	Vincent Consonni Grenoble INP - CNRS, France
11:20 - 11:45 AM	A07: Molecular Beam Epitaxy of InAs Quantum Dots Embedded in Strain-Relaxed Barriers for Ultrafast Nonlinear Optical Devices	Takahiro Kitada University of Tokushima, Japan
11:45 AM - 12:10 PM	A08: The Role of The Topmost N-H Layer For In Incorporation During InGaN MOVPE Growth	Tomoe Yayama Kyushu University, Japan
12:10 - 14:00 PM	<b>LUNCH BREAK</b>	
<b>Tuesday December 11</b>	<b>Room A: Session III</b>	<b>Chair: Dillon D. Fong</b>
14:00 - 14:25 PM	A09: Generation of Charged Gas Phase Nuclei and Their Deposition into Films, Nanowires and Nanotubes during Chemical Vapor Deposition	Nong-Moon Hwang Seoul National University, Korea
14:25 - 14:50 PM	A10: Molecular Beam Epitaxy Growth of AlAsSb/InGaAs- based Coupled Double Quantum Wells Toward All- Optical Signal Processing devices	Shin-ihiko Gozu National Institute of Advanced Industrial Science and Technologies (AIST), Japan
14:50 - 15:15 PM	A11: Complex Nanostructures of QR/QD	Somsak Panyakeow Chulalongkorn University, Thailand
15:15 - 15:40 PM	A12: Growth of Semiconductor Quantum Dots by Metal Organic Molecular Beam Epitaxy and Control of Exciton Fine Structure Splitting for Controlled Photon Emitters	Satoru Odashima Hokkaido University, Japan
15:40-16:00 PM	<b>COFFEE BREAK</b>	
<b>Tuesday December 11</b>	<b>Room A: Session IV</b>	<b>Chair: Somsak Panyakeow</b>
16:00 - 16:25 PM	A13: MBE Growth and Characterization of GaN-based Dilute Magnetic Semiconductor Nanostructures	Shigehiko Hasegawa Osaka University, Japan
16:25 - 16:50 PM	A14: Monolithic growth of multi-color InAs-QD ensembles for broadband and spectrum-shape-controllable near-infrared light source	Nobuhiko Ozaki Wakayama University, Japan
16:50 - 17:15 PM	A15: Surface Nanostructures for Elimination of Internal Reflection for Light Emitting Diodes	Jong-Lam Lee Pohang University of Science and Technology, Korea

19:30 PM	<b>DINNER</b>	
<b>2012 Collaborative Conference on Crystal Growth (3CG)</b>		
<b>Wednesday December 12</b>	<b>Room A: Session V</b>	<b>Chair: Qixin Guo</b>
8:30 - 8:55 AM	A16: Observation of group III nitride semiconductors by in situ X-ray diffraction monitoring during metalorganic vapor phase epitaxy growth	Motoaki Iwaya Meijo University, Japan
8:55 - 9:20 AM	A17: Epitaxy of AlGa <sub>N</sub> Multiple-Quantum Wells by MOVPE and Its Application of Ultraviolet Light Source	Hideto Miyake Mie University, Japan
9:20 - 9:45 AM	A18: Local Droplet Etching - Nanoholes for Quantum Dots and Nanopillars	Christian Heyn University of Hamburg, Germany
9:45 - 10:10 AM	A19: Epitaxial Growth of Dilute Nitride Semiconductor Nanostructures: d-doping Quantum Structures and Nanowires	Fumitaro Ishikawa Osaka University, Japan
10:10 - 10:30 AM	<b>COFFEE BREAK</b>	
<b>Wednesday December 12</b>	<b>Room A: Session VI</b>	<b>Chair: Christian Heyn</b>
10:30 - 10:55 AM	A20: Selective-Area Metal-Organic Vapor Phase Epitaxy of Ferromagnetic MnAs Nanoclusters and MnAs/GaAs Hybrid Nanowires	Shinjiro Hara Hokkaido University, Japan
10:55 - 11:20 AM	A21: Color-Tunable Light Emitting Germanium Nanocrystals	Naoto Shirahata National Institute for Materials Science, Japan
11:20 - 11:45 AM	A22: Theoretical Analysis for N Incorporation in GaAsN Grown by Vapor Phase Epitaxy	Jun Kawano Hokkaido University, Japan
12:10 - 14:00 PM	<b>LUNCH BREAK</b>	
<b>Wednesday December 12</b>	<b>Room A: Session VII</b>	<b>Chair: Fumitaro Ishikawa</b>
14:00 - 14:25 PM	A23: Heteroepitaxial growth of ZnTe layers by MOVPE	Qixin Guo Saga University, Japan
14:25 - 14:50 PM	A24: Computational Approach for the Growth Processes of Semiconductor Nanowires	Toru Akiyama Mie University, Japan

14:50 - 15:15 PM	A25: Stress Relaxation Mechanism of Semipolar InGaN/GaN Grown by MOVPE	Noriyuki Kuwano University of Technology Malaysia, Malaysia
15:15 - 15:40 PM	A26: Hetero- and Homo-Epitaxy of Thick AlN Layers by Hydride Vapor Phase Epitaxy	Yoshinao Kumagai Tokyo University of Agriculture and Technology, Japan
15:40-16:25 PM	<b>COFFEE BREAK &amp; POSTER REVIEW</b>	
<b>Wednesday December 12</b>	<b>Room A: Session VIII</b>	<b>Chair: Guoqiang Li</b>
16:25 - 16:50 PM	A27: Crystal growth and structural characteristics of fullerene / GaAs interfaces	Jiro Nishinaga Waseda University, Japan
16:50 - 17:15 PM	A28: Nano-cluster Assisted High Rate and High Yield Silicon Epitaxy by Mesoplasma CVD	Makoto Kambara The University of Tokyo, Japan
17:15 - 17:40 PM	A29: GaN-based Semiconductor Nanostructures for Solid State Lighting and Quantum Photonics	Yong-Hoon Cho Korea Advanced Institute of Science and Technology (KAIST), Korea
17:40 -18:05 PM	A30: Proposal of SMART III-N Tandem Solar Cells on the Basis of Coherent-Structure InN/GaN Short-Period Superlattices	Akihiko Yoshikawa Chiba University, Japan
19:30 PM	<b>DINNER RECEPTION</b>	
<b>2012 Collaborative Conference on Crystal Growth (3CG)</b>		
<b>Thursday December 13</b>	<b>Room A: Session IX</b>	<b>Chair: Holger Eisele</b>
8:30 - 8:55 AM	A31: Growth and Characterizations of GaMnN Epifilms and Nanorods	Li-Wei Tu National Sun Yat-Sen University, Taiwan
8:55 - 9:20 AM	A32: Fabrication of Sub-100 nm Stripe Patterns by I-line Interferometric Lithography For Selective Epitaxy of Semiconductor nanostructures	S. C. Lee University of New Mexico, USA
9:20 - 9:45 AM	A33: Selective Area Growth of GaN Rods and Core-shell LED Structure by MOVPE	Shunfeng Li Institute of Optoelectronics of Beijing University in Dongguan, China & Braunschweig university of technology, Germany

9:45 - 10:10 AM	A34: Crystal Growth of Semipolar/nonpolar GaN on Patterned Silicon Substrates by Metalorganic Vapor Phase Epitaxy	Tomoyuki Tanikawa Tohoku University, Japan
10:10 - 10:30 AM	<b>COFFEE BREAK</b>	
<b>Thursday December 13</b>	<b>Room A: Session X</b>	<b>Chair: Li-Wei Tu</b>
10:30 - 10:55 AM	A35: Droplet Epitaxy In Lattice-mismatched Systems	Masafumi Jo National Institute for Materials Science (NIMS), Japan
10:55 - 11:20 AM	A36: Epitaxial Growth of Highly Efficient GaN-based LEDs on Patterned Sapphire Substrates With Novelty Designed Patterns	Guoqiang Li South China University of Technology, China
11:20 - 11:45 AM	A37: Heteroepitaxial Growth of InSb on Si by Using Surface Reconstruction Controlled Epitaxy	Masayuki Mori University of Toyama, Japan
11:45 AM – 12:10 PM	A38: High-electron-mobility In <sub>0.53</sub> Ga <sub>0.47</sub> As/In <sub>x</sub> Ga <sub>1-x</sub> As composite-channel modulation-doped heterostructures grown by metal-organic vapor-phase epitaxy	Hiroki Sugiyama NTT Photonics Laboratories, Japan
12:10 - 14:00 PM	<b>LUNCH BREAK</b>	
<b>Thursday December 13</b>	<b>Room A: Session XI</b>	<b>Chair: Shunfeng Li</b>
14:00 - 14:25 PM	A39: Tensile-strained III-V semiconductor nanostructures at the atomic scale	Holger Eisele Berlin University of Technology, Germany
14:25 - 14:50 PM	A40: Solid phase epitaxy of germanium compounds	Ruben Lieten KU Leuven, Belgium
14:50 - 15:15 PM	A41: A Novel Evanescent-to-Propagating Light Transformation Effect in Sub-Wavelength-Sized Ridge Structures and its Application to Light-Emitting Diodes	Xuelun Wang National Institute of Advanced Industrial Science and Technology (AIST), Japan
15:15 - 15:40 PM	A42: Thickness-dependent structure-property correlations in coherently-grown (110) SrRuO <sub>3</sub> thin films	Daisuke Kan Kyoto University, Japan

15:40-16:00 PM	<b>COFFEE BREAK</b>	
<b>Thursday December 13</b>	<b>Room A: Session XII</b>	<b>Chair: Ruben Lieten</b>
16:00 - 16:25 PM	A43: Tunable positive magnetoresistance and high mobility in LaAlO <sub>3</sub> /SrTiO <sub>3</sub> bilayer heterostructures	Tom Wu Nanyang Technological University, Singapore
16:25 - 16:50 PM	A44: Metal Oxide Nanowires: Growth Mechanisms and Memristive Properties in a Single Oxide Nanowire	Takeshi Yanagida Osaka University
16:50 - 17:15 PM	A45: Effects of Post-Deposition Annealing Ambient on Band Alignment of RF Magnetron Sputtered Y <sub>2</sub> O <sub>3</sub> on Gallium Nitride	Kuan Yew Cheong University Sains Malaysia , Malaysia
17:15 - 17:40 PM	A46: Probing the Structural, Electrical and Mechanical Behaviors of Nano-materials by Advanced TEM techniques	Jianbo Wang Wuhan University, China
19:30 PM	<b>DINNER</b>	
<b>December 14: Social Events and Networking</b>		

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<b>Tuesday December 11 8:50 - 9:00 AM</b>	<b>Opening: ENERGY</b>	
<b>Tuesday December 11</b>	<b>Room B: Session I</b>	<b>Chair: Makoto Kobayashi</b>
9:00 – 9:25 AM	B01: Deposition and Characterization of Doped ZnO for Solar Energy Applications	Jingbiao Cui University of Arkansas at Little Rock, USA
9:25 - 9:50 AM	B02: Nanocable array photoanodes with single crystalline ZnO nanorod core and polycrystalline II–VI semiconductor shell	Hao Wang Hubei University, China
9:50 - 10:15 AM	B03: Optoelectronic and Nanogenerator Applications of ZnO Nanocrystals	Binay Kumar University of Delhi, India
10:15 - 10:30 AM	<b>COFFEE BREAK</b>	
<b>Tuesday December 11</b>	<b>Room B: Session II</b>	<b>Chair: Jingbiao Cui</b>
10:30 - 10:55 AM	B04: ZnO/Si and ZnO/GaN heterojunctions: structural, electrical and optical properties	Chang Liu Wuhan University, China
10:55 - 11:20 AM	B05: Facile Spin-Spray Method for Low-Temperature Fabrication of Metal Oxide Films	Hajime Wagata Shinshu University, Japan
11:20 - 11:45 AM	B06: Effects of Pressure on the Generation of Crystalline Silicon Gas Phase Nuclei and	Seung-Wan Yoo Seoul National University,

	Their Deposition into Films during Hot-Wire Chemical Vapor Deposition	Korea
12:10 - 14:00 PM	<b>LUNCH BREAK</b>	
<b>Tuesday December 11</b>	<b>Room B: Session III</b>	<b>Chair: Binay Kumar</b>
14:50 - 15:15 PM	B07: Synthesis of Titanium Dioxide Crystals from Water-soluble Titanium Complexes	Makoto Kobayashi Tohoku University, Japan
15:15 - 15:40 PM	B08: Fabrication of nip and pin structure GaInNAsSb solar cells	Naoya Miyashita The University of Tokyo, Japan
15:40 - 16:00 AM	<b>COFFEE BREAK</b>	
<b>Wednesday December 12</b>	<b>Room B: Session IV</b>	<b>Chair: Bo Zou</b>
16:00 - 16:25 PM	B09: Study of Cu-poor to Cu-rich transition during Cu(In,Ga)Se <sub>2</sub> growth: Grain Boundary Migration recrystallization model	Couzinie-Devy François, UMR 6502 Université de Nantes, France
16:25 - 16:50 PM	B10: The effect of heavily Ge codoping on grown-in micro defects and photovoltaic characteristics of B- doped CZ-Si	Mukkannan Arivanandhan Shizuoka University, Japan
19:30 PM	<b>DINNER</b>	
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<b>Wednesday December 12</b>	<b>Room B: Session V</b>	<b>Chair: Anne Pillonnet</b>
9:00 - 9:25 AM	B11: Stretchable Power Sources for Flexible Electronics	Bingqing Wei University of Delaware, USA
9:25 - 9:50 AM	B12: Synthesis, growth, structural, spectral, thermal, linear and nonlinear optical and mechanical studies of a new organic nonlinear optical single crystal 4-Chloro 4-Nitrostilbene (CONS)	S. Kalainathan VIT University, India
9:50 - 10:15 AM	B13: Mixed-Oxide Crystals Grown For Solar Energy Conversion Applications	Krzysztof Bienkowski Warsaw University, Poland
10:15 - 10:30 AM	<b>COFFEE BREAK</b>	



<b>Wednesday December 12</b>	<b>Room B: Session VI</b>	<b>Chair: Bingqing Wei</b>
10:30 - 10:55 AM	B14: Synthesis of Amphiphilic Brookite Nanocrystals with High Photocatalytic Performance	Kenichi Katsumata Tokyo Institute of Technology, Japan
10:55 - 11:20 AM	B15: Growth of plasmonic luminophor films for photovoltaic applications	Anne Pillonnet UMR5620 CNRS-UCBL- Université de Lyon, France
11:20 - 11:45 AM	B16: Crystal Growth of Functional Nanomaterials in Ultrasound and Microwave-assisted Syntheses	Jun-Jie Zhu Nanjing University, China
12:10 - 14:00 PM	<b>LUNCH BREAK</b>	
<b>Wednesday December 12</b>	<b>Room B: Session VII</b>	<b>Chair: Hirokazu Tatsuoka</b>
14:50 - 15:15 PM	B17: Polycrystalline Silicon Films Formed by Flash Lamp Annealing for Solar Cell Application	Keisuke Ohdaira Japan Advanced Institute of Science and Technology, Japan
15:15 - 15:40 PM	B18: Highly oriented metal-organic framework nanosheets assembled on liquid/air interfaces	Rie Makiura Osaka Prefecture University, Japan
15:40 - 16:25 PM	<b>COFFEE BREAK &amp; POSTER REVIEW</b>	
<b>Wednesday December 12</b>	<b>Room B: Session VIII</b>	<b>Chair: Rie Makiura</b>
16:25 - 16:50 PM	B19: Simple Fabrication and Structural Modification of Silicide, Oxide and Metallic Nanostructures by Thermal Treatment	Hirokazu Tatsuoka Shizuoka University, Japan
16:50 - 17:15 PM	B20: Characterization of ZnO films deposited by sol-gel technique	In-Sung Park Hanyang University, Seoul, Korea
17:15 - 17:40 PM	B21: Partial Influencing factors of Novel Semiconductor Nanocrystals Growth: Pressure, Reaction Temperature, Reaction Time, Heating Rate and Precursor	Bo Zou Jilin University, China
19:30 PM	<b>DINNER RECEPTION</b>	

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<b>Thursday December 13</b>	<b>Room B: Session IX</b>	<b>Chair: Isao Ohkubo</b>
9:00 - 9:25 AM	B22: Novel optical functionalities on metal oxide nanomaterials	Shin-ichi Ohkoshi The University of Tokyo, Japan
9:25 - 9:50 AM	B23: Nanoalloys: from core-shell nanostructures to ordered alloys	Marie-Jose Casanove CEMES - CNRS, France
9:50 - 10:15 AM	B24: Phase selective crystal growth of colloidal ZnSe nanocrystals	Takahisa Omata Osaka University, Japan
10:15 - 10:30 AM	<b>COFFEE BREAK</b>	
<b>Thursday December 13</b>	<b>Room B: Session X</b>	<b>Chair: Ryota Takahashi</b>
10:30 - 10:55 AM	B25: Real time Atomic Force Microscopy imaging versus transport measurements during nanogap fabrication by electromigration	Jean-Luc Bubendorff Institut de Science des Matériaux de Mulhouse (IS2M), CNRS-UHA, France
10:55 - 11:20 AM	B26: Fabrication and Functionalities of MgO (111) and (100) thin films	Tomofumi Susaki Tokyo Institute of Technology, Japan
11:20 - 11:35 AM	B27: Modelling of Mixed-Metal Oxides Photoanodes for Water Splitting Purposes	Renata Solarska Warsaw University, Warsaw, Poland
11:35 - 11:50 AM	B28: Effects of high magnetic fields on the microstructure and magnetostriction of TbFe <sub>2</sub> based alloy during solidification process	Tie Liu Northeastern University, China
12:10 - 14:00 PM	<b>LUNCH BREAK</b>	
<b>Thursday December 13</b>	<b>Room B: Session XI</b>	<b>Chair: Kathy Kash</b>

14:00 - 14:25 PM	B29: Influencing the Crystalline Structure of FePt nanoColloids with Ionic Liquids	Pascal André University of St Andrews, United Kingdom
14:25 - 14:50 PM	B30: Thermophysical Property Measurement of Molten Semiconductors and Metals by an Electromagnetic Levitator Superimposed with a Static Magnetic Field	Takao Tsukada Tohoku University, Japan
14:50 - 15:15 PM	B31: Synthesis, modification of Single-Crystal Rutile TiO <sub>2</sub> Nanorod Arrays and Its Application for Quantum-Dot Sensitized Solar Cells	Xiaodong Fang Chinese Academy of Science, China
15:15 - 15:40 PM	B32: Effect of in situ application of high magnetic fields on the growth of the molecular beam vapor deposited Ni-Fe nanocrystalline films	Qiang Wang Northeastern University, China
15:40-16:00 PM	<b>COFFEE BREAK</b>	
<b>Thursday December 13</b>	<b>Room B: Session XII</b>	<b>Chair: Marek Szafranski</b>
16:00 - 16:25 PM	B33: Development of the Zn-IV-Nitride Semiconductors	Kathleen Kash Case Western Reserve University, USA
16:25 - 16:50 PM	B34: Epitaxial growth of complex oxides toward novel spintronics devices	Isao Ohkubo National Institute for Materials Science (NIMS), Japan
16:50 - 17:15 PM	B35: Control of Carrier Type in Half-Metallic Spinel Ferrite Thin Films	Munetoshi Seki The University of Tokyo, Japan
17:15 - 17:40 PM	B36: In-situ control of oxide surfaces during pulsed laser deposition	Thomas Tybell Norwegian University of Science and Technology (NTNU), Norway
19:30 PM	<b>DINNER</b>	
<b>2012 Collaborative Conference on Crystal Growth (3CG)</b>		
<b>Friday December 14</b>	<b>Room B: Session XIII</b>	<b>Chair: Qiang Wang</b>

9:00 - 9:25 AM	B37: Self-template Growth of Multiferroic Magnetite Films and Nano-pyramids	Ryota Takahashi University of Tokyo, Japan
9:25 - 9:50 AM	B38: New ferroelectric phases in guanidinium complexes	Marek Szafranski Adam Mickiewicz University, Poland
9:50 - 10:15 AM	B39: Integration of functional oxides with semiconductors	Romain Bachelet Lyon Institute of Nanotechnology (INL-CNRS), France
10:15 - 10:40 AM	B40: To be determined	M. Navaneethan Shizuoka University, Japan
<b>10:40 - 10:50 AM</b>	<b>Closing</b>	

**December 14 Afternoon: Social Events and Networking**

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December 10

<b>Tuesday December 11 8:50 - 9:00 AM</b>	<b>Opening: CRYSTAL</b>	
<b>Tuesday December 11</b>	<b>Room C: Session I</b>	<b>Chair: George S. Nolas</b>
9:00 - 9:25 AM	C01: Si <sub>0.5</sub> Ge <sub>0.5</sub> Bulk Single Crystal Growth by the Traveling Liquidus-Zone Method	Kyoichi Kinoshita Japan Aerospace Exploration Agency, Japan
9:25 - 9:50 AM	C02: Liquid Phase Diffusion Growth of SiGe Single Crystals	Sadik Dost University of Victoria, Canada
9:50 - 10:15 AM	C03: Defect studies in Si -Questions on current topics for crystal growth of CZ-Si	Ichiro Yonenaga Tohoku University, Japan
10:15 - 10:30 AM	<b>COFFEE BREAK</b>	
<b>Tuesday December 11</b>	<b>Room C: Session II</b>	<b>Chair: Ichiro Yonenaga</b>
10:30 - 10:55 AM	C04: Growth and Property of Carbon Nanotubes formed on SiC by Thermal Decomposition	Takahiro Maruyama Meijo University, Japan

10:55 - 11:20 AM	C05: New Crystal Growth Techniques in Investigating Single-crystal Inorganic Clathrates	George S. Nolas University of South Florida, USA
11:20 - 11:45 AM	C06: Growth and characterization of germanium crystals from B <sub>2</sub> O <sub>3</sub> -covered melt	Toshinori Taishi Shinshu University, Japan
<b>LUNCH BREAK</b>		
<b>Tuesday December 11</b>	<b>Room C: Session III</b>	<b>Chair: Kyoichi Kinoshita</b>
14:50 - 15:15 PM	C07: Crystal growth of core/shell zeolite composites	Angélique Simon-Masseron Univ de Haute Alsace (UHA), France
15:15 - 15:40 PM	C08: Synthesis and thermal stability of metastable copper oxide thin films	Jean-François Pierson University of Lorraine, France
15:40 - 16:00 AM	<b>COFFEE BREAK</b>	
<b>Tuesday December 11</b>	<b>Room C: Session IV</b>	<b>Chair: Angélique Simon-Masseron</b>
16:00 - 16:25 PM	C09: Growth control of CaCO <sub>3</sub> crystal by impurities: a molecular dynamics study	Hiroki Nada National Institute of Advanced Industrial Science and Technology, Japan
16:25 - 16:50 PM	C10: Flux Growth and Characterization of Some Complex Perovskite PbB <sup>1/2</sup> B <sup>1/2</sup> O <sub>3</sub> Single Crystals	Antoni Kania University of Silesia, Poland
19:30 PM	<b>DINNER</b>	
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<b>Wednesday December 12</b>	<b>Room C: Session V</b>	<b>Chair: Liliana Dobrzanska</b>
9:00 - 9:25 AM	C11: Expanded Crystalline Fulleride Superconductors	Kosmas Prassides Durham University, UK

9:25 - 9:50 AM	C12: Engineering Non-centrosymmetric Structures using p—p Stacking	Graham Saunders The University of Waikato, New Zealand
9:50 - 10:15 AM	C13: Pentacene Donor Substrate Synthesized by PLD for LIFT Process	Yannick Larmande Université Claude Bernard Lyon 1, France
10:15 - 10:30 AM	<b>COFFEE BREAK</b>	
<b>Wednesday December 12</b>	<b>Room C: Session VI</b>	<b>Chair: Graham Saunders</b>
10:30 - 10:55 AM	C14: Crystal engineering of metal complexes with imidazole-containing ligands	Wei-Yin Sun Nanjing University, China
10:55 - 11:20 AM	C15: Single-crystal-to-single-crystal transformations triggered by external stimuli	Liliana Dobrzanska University of Stellenbosch, South Africa
11:20 - 11:45 AM	C16: Crystal growth and second harmonic generation efficiencies of some chalcone derivatives	SP. Meenakshisundaram Annamalai University, India
	<b>LUNCH BREAK</b>	
<b>Wednesday December 12</b>	<b>Room C: Session VII</b>	<b>Chair: Kosmas Prassides</b>
14:00 – 14:25 PM	C17: Silent Features of Physical Chemistry in Crystal Growth Technology	Ramanand Rai Banaras Hindu University, India
14:25 – 14:50 PM	C18: Superhydrophobic surface: basics and its easy-to-clean and antibacterial applications	Xiaoxue Zhang Tampere University of Technology, Finland
14:50 - 15:15 PM	C19: Unanticipated crystallization of amorphous silicon nitride precipitates in ferrite	Hugo Van Landeghem Institut Jean Lamour - CNRS - UMR7198, France
15:15 - 15:40 PM	C20: Fabrication of Orientation Controlled Mordenite Seed Layer on Porous Ceramic Substrate in Strong Magnetic Field	Tetsuo Uchikoshi National Institute for Materials Science, Japan
15:40 - 16:25 PM	<b>COFFEE BREAK &amp; POSTER REVIEW</b>	
<b>Wednesday December 12</b>	<b>Room C: Session VIII</b>	<b>Chair: Hugo Van Landeghem</b>

16:25 - 16:50 PM	C21: Kinetic study of the oxalic precipitation of actinides	Murielle Bertrand French Alternative Energies and Atomic Energy Commission, France
16:50 - 17:15 PM	C22: Solution Growth of Silicon Carbide: An Old process revisited.	Didier Chaussende Institut Polytechnique de Grenoble, France
17:15 - 17:40 PM	C23: Are packing fragments of crystals from biological macromolecules prone to aggregation?	Dominique Maes Vrije Universiteit Brussel (VUB), Belgium
19:30 PM	<b>DINNER RECEPTION</b>	
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<b>Thursday December 13</b>	<b>Room C: Session IX</b>	<b>Chair: Xiaoxue Zhang</b>
9:00 - 9:25 AM	C24: Formation Mechanism of Polyhedral Topological Crystals	Masakatsu Tsubota Hokkaido University, Japan
9:25 - 9:50 AM	C25: An Organic Crystal Engineering Using Hydrogen Bonding Chain of Trifluorolactates for Construction of Tunnel Microporous Crystals	Toshimasa Katagiri Okayama University, Japan
9:50 - 10:15 AM	C26: Hydrothermal Growth and Structural Studies of Si <sub>1-x</sub> GexO <sub>2</sub> Single Crystals	Alain Largeteau ICMCB-CNRS UPR 9048 & IPB / ENSCBP, France
10:15 - 10:30 AM	<b>COFFEE BREAK</b>	
<b>Thursday December 13</b>	<b>Room C: Session X</b>	<b>Chair: Masaharu Oshima</b>
10:30 - 10:55 AM	C27: Single Crystal growth of Chalcopyrite and Kesterite Compounds by Traveling Heater Method	Akira Nagaoka University of Miyazaki, Japan
10:55 - 11:20 AM	C28: Numerical simulation of crystallization processes for the production of silicon for photovoltaic applications	Martin P. Bellmann SINTEF Materials and Chemistry, Norway



11:20 - 11:45 AM	C29: Localized growth of p-doped SiC by Vapour-Liquid-Solid transport: a technological step towards new wide bandgap devices	Davy Carole Université Claude Bernard Lyon1, France
11:45 AM – 12:10 PM	C30: Growth of near IR quaternary Ag-Ga-Ge-Se semiconductor single crystals	Mythili Prakasam ICMCB-CNRS, Pessac, France
12:10 - 14:00 AM	<b>LUNCH BREAK</b>	
<b>Thursday December 13</b>	<b>Room C: Session XI</b>	<b>Chair: Takumi Konno</b>
14:00 - 14:25 PM	C31: Synchrotron Radiation Nano-Spectroscopy for Power Efficient Oxide Electronics Devices	Masaharu Oshima The University of Tokyo, Japan
14:25 - 14:50 PM	C32: MPB Design and Crystal Growth of PMN-PT Based High Trt Relaxor Ferroelectrics	Qiang Li Tsinghua University, China
14:50 - 15:15 PM	C33: Mg-doped lithium niobate and lithium tantalate crystal with stoichiometric structure grown from the congruent melt	Satoshi Uda Tohoku University, Japan
15:15 - 15:40 PM	C34: Supramolecular architectures formation and their functionalities based on thiacalixarene system	Fumio Hamada Akita University, Japan
15:40-16:00 PM	<b>COFFEE BREAK</b>	
<b>Thursday December 13</b>	<b>Room C: Session XII</b>	<b>Chair: Qiang Li</b>
16:00 - 16:25 PM	C35: Self-organization of D-Penicillaminato Metal Clusters into Metallosupraomlecular Architectures	Takumi Konno Osaka University, Japan
16:25 - 16:50 PM	C36: Growth and spectroscopic properties of newly flux grown RE <sub>2</sub> O <sub>3</sub> :Yb <sup>3+</sup> (RE=Y,Gd,Lu) laser crystals for high-power and/or short-pulse diode-pumped systems	Matias Velazquez Université de Bordeaux, ICMCB, France
16:50 - 17:15 PM	C37: Oriented Nucleation and Growth of Sr <sub>2</sub> TiSi <sub>2</sub> O <sub>8</sub> –Fresnoite in Glass-Ceramics	Wolfgang Wisniewski Jena University, Germany

17:15 - 17:40 PM	C38: Growth LiNbO3 Single Crystals for PPLN applications based on Wet-chemical Polycrystalline Powder Synthesis and Hang-crucible Growth Technique	Hong Liu Shandong University, China
19:30 PM	<b>DINNER</b>	
<b>2012 Collaborative Conference on Crystal Growth (3CG)</b>		
<b>Friday December 14</b>	<b>Room C: Session XIII</b>	<b>Chair: Wolfgang Wisniewski</b>
9:00 - 9:25 AM	C39: Progress on the Photoelectronic Functional Crystals in China	Jiyang Wang Shandong University, China
9:25 - 9:50 AM	C40: NPLIN : a new experimental device for LASER induced nucleation	Anne Spasojevic -de Biré Ecole Centrale Paris, France
9:50 - 10:15 AM	C41: Atomistic investigation of SiC/SiO2 interfaces for the SiC-MOSFET power devices	Kenji Shiraishi Tsukuba University, Japan
10:15 - 10:40 AM	C42: Atomically smooth damage free finishing of 4H-SiC(0001) by plasma assisted polishing	Kazuya Yamamura Osaka University, Japan
10:40 – 10:50 AM	<b>Closing</b>	
<b>December 14 Afternoon: Social Events and Networking</b>		

# 2012 Collaborative Conference on Crystal Growth (3CG)

December 11-14, 2012

Doubletree by Hilton Orlando at SeaWorld, Orlando, Florida, USA

**Wednesday**

**December 12**

**15:40- 16:25 PM**

## Poster Review

**P1: Photoluminescence in GaNAs(Sb) thin films and carrier localization**

**Nazmul Ahsan**  
The University of Tokyo,  
Japan

**P2: Photoreversible magnetism in a bistable metal-cyanide polymer**

**Hiroko Tokoro**  
The University of Tokyo,  
Japan

**P3: Non Photochemical Light Induced Nucleation of Carbamazepine in Polar protic and aprotic solvents**

**Aziza. Ikni**  
Ecole Centrale Paris, France

**P4: Understanding photophysical effects : NPLIN on glycine and L - glutamic acid**

**Bertrand Clair**  
Ecole Centrale Paris, France

**P5: Direct growth of LiCoO<sub>2</sub>/Al-Co layered double hydroxide film on Al substrate**

**Takahiro Ishizaki**  
Shibaura Institute of  
Technology, Japan

**P6: Green Synthesis of Fluorescent Silver Nanoclusters and Enhanced Fluorescent with [HOEtMIm][BF<sub>4</sub>] Ionic Liquid**

**Feng Lu**  
Nanjing University, China

**P7: How near field microscopy techniques help to understand corrosion phenomena: the case of stainless steels and nickel-based alloys**

**Jean-Luc Bubendorff**  
Institut de Science des  
Matériaux de Mulhouse  
(IS2M), CNRS-UHA, France

**P8: Deposition Control of the epitaxial orientation and reduction of the interface leakage current in YMnO<sub>3</sub>/GaN heterostructures**

**Chang Liu**  
Wuhan University, China